

# Highly Efficient, Regulated Dual-Output, Ambient Energy Manager for AC or DC Sources with Optional Primary Battery

## **Features**

#### Ultra-low power start-up

- Cold start from 380 mV input voltage and 3  $\mu$ W input power (typical).

#### Ultra-low power boost regulator

- Open-circuit voltage sensing for MPPT every 0.33 s.
- Configurable MPPT with 2-pin programming.
- Selectable Voc ratios of 50%, 65% or 80%.
- Harvesting input voltage range from 50 mV to 5 V.
- MPPT voltage operation range from 50 mV to 4.5 V.
- Constant impedance matching (ZMPPT).

#### Integrated 1.2 V/1.8 V LDO regulator

- Up to 20 mA load current.
- Dynamically power-gated by external control.
- Selectable output voltage.

#### Integrated 1.8 V - 4.1 V LDO regulator

- Up to 80 mA load current with 300 mV drop-out.
- Dynamically power-gated by external control.
- Selectable or adjustable output voltage.

#### Flexible energy storage management

- Selectable or adjustable overcharge and overdischarge protection for any type of rechargeable battery or (super)capacitor.
- Fast supercapacitor charging.
- Indication when battery is running low.
- Indication when output voltage regulators are available.

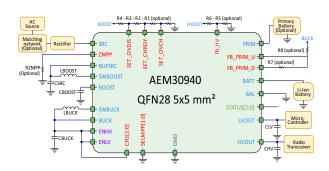
#### Optional primary battery

 Automatic switching to primary battery when the secondary battery is exhausted.

Integrated storage element balancing circuit for dual-cell supercapacitor

## **Applications**

Piezo harvesting	Home automation
Micro turbine harvesting	Transportation
RF harvesting	Smart agriculture
Industrial monitoring	



## **Description**

The AEM30940 is an integrated energy management circuit that extracts DC power from a piezo generator, a micro turbine generator or any high frequency RF input to simultaneously store energy in a rechargeable element and supply the system with two independent regulated voltages. The AEM30940 allows to extend battery lifetime and ultimately eliminate the primary energy storage element in a large range of wireless applications such as industrial monitoring, home automation, transportation and smart agriculture.

The AEM30940 harvests the available input current up to 110 mA while regulating the source to a voltage configured by the user. It integrates an ultra-low power boost converter to charge a storage element, such as a Li-ion battery, a thin film battery, a supercapacitor or a conventional capacitor. The boost converter operates with input voltages ranging from 50 mV to 5 V.

With its unique cold-start circuit, it can start operating with empty storage elements at an input voltage as low as 380 mV and an input power of only 3  $\mu$ W.

The low-voltage supply typically drives a microcontroller at 1.2 V or 1.8 V. The high-voltage supply typically drives a radio transceiver at a configurable voltage between 1.8 V and 4.1 V. Both are driven by highly-efficient LDO (Low Drop-Out) linear regulators for low noise and high stability.

Configuration pins determine various operating modes by setting predefined conditions for the energy storage element (overcharge or overdischarge voltages), and by selecting the voltage of the high-voltage supply and the low-voltage supply. Moreover, special modes can be obtained at the expense of a few configuration resistors.

The chip integrates all active elements for powering a typical wireless sensor. Five capacitors and two inductors are required, all available in small packages. With only seven external components, integration is maximized, footprint and BOM are minimized, optimizing the time-to-market and the costs of designs.

## **Device Information**

Part Number	Package	Body Size
10AEM30940C0000	QFN 28-pin	5x5mm

#### **Evaluation Board**

AEM30940 evaluation boards are available at e-peas.com.



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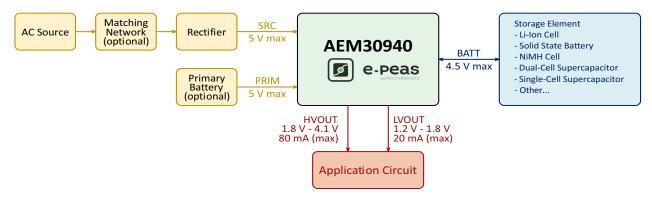


Figure 1: Simplified schematic view

#### 1. Introduction

The AEM30940 is a full-featured energy efficient power management circuit capable of charging a storage element (battery or supercapacitor, connected to BATT) from an energy source (connected to SRC) as well as supplying loads at different operating voltages through two power supplying LDO regulators (LVOUT and HVOUT).

The heart of the AEM30940 is a cascade of two regulated switching converters, namely the boost converter and the buck converter, both with high power conversion efficiencies (See Section 12).

At first start-up, as soon as a required cold-start voltage of 380 mV and a scant amount of power of only 3  $\mu W$  are available from the harvested energy source, the AEM coldstarts. After the cold start, the AEM can extract the power available from the source as long as the input voltage is within 50 mV to 5 V range.

Through three configuration pins (CFG[2:0]), the user can select a specific operating mode from a range of seven modes that covers most application requirements without any dedicated external component. These operating modes define the LDO output voltages and the protection levels of the storage element. A custom mode allows the user to define arbitrary storage element protection levels and the output voltage of the high-voltage LDO (See Section 9.1).

The Maximum Power Point (MPP) ratio can be configured using two configuration pins (SELMPP[1:0]) (See Section 9.2).

Two logic control pins (ENLV and ENHV) allow to dynamically activate or deactivate the LDO regulators that supply the low and high voltage load. The status pin STATUS[0] alerts the user that the LDOs are operational and can be enabled. This signal can also be used to enable an optional external regulator.

If the battery voltage gets depleted, LVOUT and HVOUT are power-gated and the controller is no longer supplied by the storage element to protect it from further discharge. Around 600 ms before the shutdown of the AEM, the status pin STATUS[1] alerts the user for a clean shutdown of the system.

However, if the storage element gets depleted and an optional primary battery is connected on PRIM, the AEM30940 automatically uses it as a source to recharge the storage element before switching back to the ambient source. This guarantees continuous operation even under the most adverse conditions (See Section 8.2.4). STATUS[1] is asserted when the primary battery is providing power.

The status of the MPPT controller is reported with one dedicated status pin (STATUS[2]). The status pin is asserted when an MPP calculation is being performed.



## 2. Pin Configuration and Functions

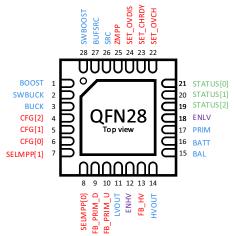


Figure 2: Pinout diagram QFN 28-pin

Name	Pin Number	Function	
Power pins			
BOOST	1	Output of the boost converter.	
SWBUCK	2	Switching node of the buck converter.	
BUCK	3	Output of the buck converter.	
LVOUT	11	Output of the low voltage LDO regulator.	
HVOUT	14	Output of the high voltage LDO regulator.	
BAL	15	Connection to the mid-point of a dual-cell supercapacitor (optional).  Must be connected to GND if not used.	
BATT	16	Connection to the energy storage element, battery or capacitor. Cannot be left floating.	
PRIM	17	Connection to the primary battery (optional).  Must be connected to GND if not used.	
SRC	26	Connection to the harvested energy source.	
BUFSRC	27	Connection to an external capacitor buffering the boost converter input.	
SWBOOST	28	Switching node of the boost converter.	
Configuration pins			
CFG[2]	4		
CFG[1]	5	Used for the configuration of the threshold voltages of the energy storage element and the output voltage of the LDOs.	
CFG[0]	6		
SELMPP[1]	7	Used for the configuration of the MPP ratio.	
SELMPP[0]	8	oscuror the configuration of the Will Tatio.	
FB_PRIM_D	9	Used for the configuration of the primary battery overdischarge voltage (optional).	
FB_PRIM_U	10	Must be connected to GND if not used.	
FB_HV	13	Used for the configuration of the high-voltage LDO when in custom mode (optional). Must be left floating if not used.	
SET_OVCH	22	Used for the configuration of the threshold voltages for the energy storage element when	
SET_CHRDY	23	in custom mode (optional).  Must be connected to BUCK if not used.	
SET_OVDIS	24		
ZMPP	25	Used for the configuration of the ZMPPT (optional).  Must be left floating if not used.	

Table 1: Pins description (Part 1)



Name	Pin Number	Function	
Control pins			
ENHV	12	Enabling pin for the high-voltage LDO (See Table 7).	
ENLV	18	Enabling pin for the low-voltage LDO (See Table 7).	
Status pins			
STATUS[2]	19	Logic output. Asserted when the AEM performs a MPP evaluation.	
STATUS[1]	20	Logic output. Asserted during 600 ms if the battery voltage falls below V <sub>OVDIS</sub> or asserted as long as the AEM is taking energy from the primary battery.	
STATUS[0]	21	Logic output. Asserted when the LDOs can be enabled.	
Other pins			
GND	Exposed pad	Ground connection, should be solidly tied to the PCB ground plane.	

Table 1: Pins description (Part 2)

# 3. Absolute Maximum Ratings

Parameter	Rating
Voltage on SRC, BUFSRC, BATT, BAL, PRIM, BOOST, SWBOOST, HVOUT, ENLV, ZMPP	5.5 V
Voltage on BUCK, SWBUCK, LVOUT, CFG[2:0], FB_PRIM_U, FB_PRIM_D, SELMPP[1:0], SET_OVDIS, SET_CHRDY, SET_OVCH, ENHV	2.75 V
Voltage on FB_HV	2.5 V
Operating junction temperature	-40°C to +125°C
Storage temperature	-65°C to +150°C

Table 2: Absolute maximum ratings

## 4. Thermal Resistance

Package	θЈА	θЈС	Unit
QFN 28-pin	38.3	2.183	°C/W

Table 3: Thermal data

ESD CAUTIO	N		
	ESD (ELECTROSTATIC DISCHARGE) SENSITIVE DEVICE These devices have limited built-in ESD protection and damage may thus occur on devices subjected to high-energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality		
VESD	Human-body model according to Jedec JS001-2017	± 500 V	
VESD	Charge device model according to Jedec JS002-2014	± 1000 V	

Table 4: ESD caution



# 5. Typical Electrical Characteristics at 25 °C

Symbol	Parameter	Condition	Min	Тур	Max	Unit	
Input voltage a	nd input power						
P <sub>SRC_CS</sub>	Source power required to coldstart.	During cold start.	3			μW	
V	Input voltage of the energy source	During cold start.	0.38		5	V	
V <sub>SRC</sub>	(maximum given by the open-circuit voltage).	After cold start.	0.05 <sup>1</sup>		5		
1	Harvested current from the energy source.	L <sub>BOOST</sub> = 10 μH.			110	mA	
I <sub>SRC</sub>	Traivested current from the energy source.	L <sub>BOOST</sub> = 22 μH.			50		
V <sub>MPP</sub>	Voltage level of the Maximum Power Point.	After cold start.	0.05		4.5	V	
DC-DC converte	ers						
V <sub>BOOST</sub>	Output voltage of the boost converter.	During normal aparation	2.2		4.5	V	
V <sub>BUCK</sub>	Output voltage of the buck converter.	- During normal operation.	2	2.2	2.5	]	
1	Total load current supplied by the BUCK	L <sub>BUCK</sub> = 10 μH.	0		20	mA	
I <sub>BUCK</sub>	converter (including LVOUT current I <sub>LV</sub> ).	L <sub>BUCK</sub> = 4 μH.	0		50	mA	
Storage elemen	nt						
V <sub>BATT</sub>	Voltage on the storage element.		02		4.5	V	
V <sub>PRIM</sub>	Voltage on the primary battery.		0.6		4.5	V	
I <sub>PRIM</sub>	Current from the primary battery.			20		mA	
V <sub>FB_PRIM_U</sub>	Feedback for defining the overdischarge voltage level on the primary battery.		0.15		1.1	V	
V <sub>OVCH</sub>	Maximum voltage accepted on the storage element before disabling the boost converter.	See Table 8.	2.3		4.5	V	
V <sub>CHRDY</sub>	Minimum voltage required on the storage element before enabling the LDO when coming from WAKE-UP MODE.	After cold start See Table 8.	2.25		4.45	V	
V <sub>OVDIS</sub>	Minimum voltage accepted on the storage element before switching to primary battery or entering SHUTDOWN MODE.	See Table 8.	2.2		4.4	V	
	Quiescent current on BATT when the boost	V <sub>BATT</sub> = 3 V; LDOs disabled.		400		nA	
IQ	converter is not running.	V <sub>BATT</sub> = 3 V; LDOs enabled.		600		nA	
Low-Voltage LD	OO regulator	· 					
V <sub>LV</sub> <sup>3</sup>	Output voltage of the low-voltage LDO.	See Table 8.	1.2		1.8	V	
I <sub>LV</sub>	Load current supplied by the low-voltage LDO.	L <sub>BUCK</sub> = 10 μH.	0		20	mA	
High-Voltage L	OO regulator						
V <sub>HV</sub> <sup>4</sup>	Output voltage of the high-voltage LDO.	See Table 8.	1.8		V <sub>OVDIS</sub> - 0.3 V	V	
I <sub>HV</sub>	Load current supplied by the high-voltage LDO.		0		80	mA	

Table 5: Electrical characteristics (Part 1)



Symbol	Parameter	Condition	Min	Тур	Max	Unit
Timing						
T <sub>MPPT,VOC</sub>	Time during which the AEM30940 stops pulling current on SRC to measure the harvester open circuit voltage (V <sub>OC</sub> ).			5.12		ms
T <sub>MPPT,PERIOD</sub>	Period of the MPPT V <sub>OC</sub> evaluations.			0.33		S
T <sub>CRIT</sub>	Time before shutdown once STATUS[1] has been asserted (see Section 8.2.5 and Figure 5).		400	600	800	ms
Logic output pins						
STATUS[2:0]	Logic output levels on the status pins.	Logic HIGH (H).	V <sub>BATT</sub> - 0.1	V <sub>BATT</sub>	V <sub>BATT</sub> + 0.1	V
31A103[2.0]		Logic LOW (L).	GND - 0.1	GND	GND + 0.1	V

Table 5: Electrical characteristics (Part 2)

- 1. Minimum  $V_{SRC}$  value for harvesting capabilities after coldstart.
- 2. To stay in NORMAL MODE,  $V_{BATT}$  minimum voltage must stay above  $V_{OVDIS}$ .
- 3. The variability of  $V_{LV}$  at 1 mA is 1% (typical and preliminary result from simulations).
- 4. The variability of  $V_{\rm HV}$  at 1 mA is 1.3% (typical and preliminary result from simulations).



# **6. Recommended Operation Conditions**

Symbol	Parameter	Parameter				Unit
External compon	ents		,	'	'	
C <sub>SRC</sub>	BUFSRC pin decoupling capacitor.	BUFSRC pin decoupling capacitor.				μF
C <sub>BOOST</sub>	Output capacitor of the boost converter.		10	22		μF
L <sub>BOOST</sub>	Inductor of the boost converter.		4	10		μН
C <sub>BUCK</sub>	Output capacitor of the buck converter.		8	10		μF
L <sub>BUCK</sub>	Inductor of the buck converter.		4	10	25	μН
C <sub>LV</sub>	Low-voltage LDO regulator decoupling ca	pacitor.	8	10	14	μF
C <sub>HV</sub>	High-voltage LDO regulator decoupling co	apacitor.	8	10	14	μF
C <sub>BATT</sub>	Optional - Capacitor connected on BATT if no storage element is connected (see	LDOs disabled.	22			μF
CBATT	Section 9.5 and Section 9.7).	LDOs enabled.	150			μF
R <sub>T</sub>	Optional - Sum of resistors for setting bathreshold voltages in custom mode.  R <sub>T</sub> = R1 + R2 + R3 + R4 (see Section 9.1).				100	ΜΩ
R <sub>V</sub>	Optional - Sum of resistors for setting the the high-voltage LDO in custom mode.  R <sub>V</sub> = R5 + R6 (see Section 9.1).					ΜΩ
R <sub>ZMPP</sub>	Optional - Resistor for the ZMPPT configu (see Section 9.4).	Optional - Resistor for the ZMPPT configuration (see Section 9.4).				
R <sub>P</sub>	Optional - Sum of resistors used to define minimum voltage.  R <sub>P</sub> = R7 + R8 (see Section 9.3).	1				
Logic input pins						
ENILLY/	Enabling pin for the high-voltage LDO.	Logic HIGH (H).	Connect to BUCK.			
ENHV	Litabiling pilitor the high-voltage LDO.	Logic LOW (L).	Connect to GND.			
ENLV	Enabling pin for the low-voltage LDO.	Logic HIGH (H).	Connect to BUCK or BOOST.			
EINLV	Enabling pin for the low-voltage LDO.	Logic LOW (L).	Connect to GND.			
CFG[2:0]	Configuration pins for the storage element protection threshold voltages	Logic HIGH (H).	Connect to BUCK.			
J. J[2.0]	(see Table 8).	Logic LOW (L).	Connect to GND.			
CELMADD[1:0]	Configuration pins for the MPPT ratio	Logic HIGH (H).	Connect to BUCK.			
SELMPP[1:0]	(see Table 9).	Logic LOW (L).	Connect to GND.			

Table 6: Recommended operating conditions



## 7. Functional Block Diagram

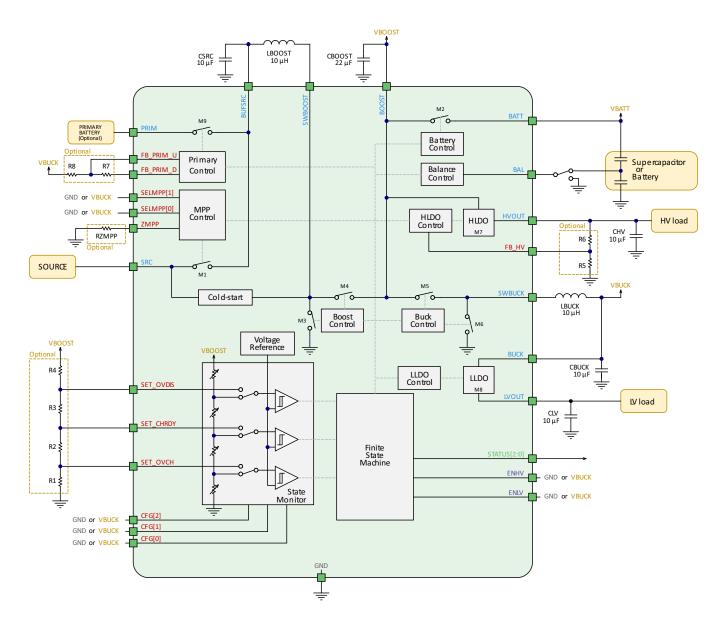


Figure 3: Functional block diagram



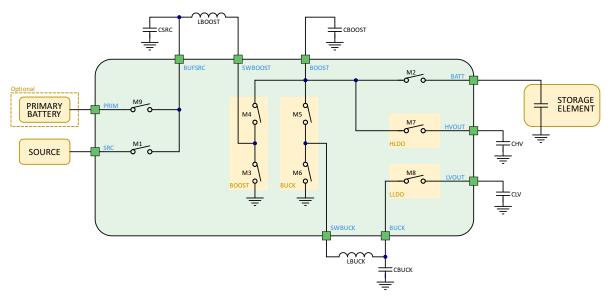


Figure 4: Simplified schematic view of the AEM30940

## 8. Theory of Operation

#### 8.1. Power Converters

#### 8.1.1. Boost Converter

The boost (or step-up) converter raises the voltage available at BUFSRC to a level suitable for charging the storage element, in the range of 2.2 V to 4.5 V, according to the system configuration. This voltage ( $V_{BOOST}$ ) is available at the BOOST pin.

The switching transistors of the boost converter are M3 and M4, with the switching node available externally at SWBOOST. The reactive power components of this converter are the external inductor  $L_{\text{BOOST}}$  and the external capacitor  $C_{\text{BOOST}}$ .

The MPPT control circuit (see Section 8.4) periodically disconnects the source on SRC pin from the BUFSRC pin with the transistor M1 in order to measure the open-circuit voltage of the harvester on SRC and define the optimal SRC regulation voltage.

BUFSRC is decoupled by the capacitor C<sub>SRC</sub>, which smooths the voltage against the current pulses induced by the boost converter.

The storage element is connected to the BATT pin. Its voltage is named  $V_{BATT}$ . This node is linked to BOOST through the transistor M2. In NORMAL MODE (see Section 8.2.2), this transistor effectively shorts the battery to the BOOST node ( $V_{BATT} = V_{BOOST}$ ). When energy harvesting is occurring, the boost converter delivers a current that is shared between the battery and the LDOs. M2 is opened to disconnect the storage element when  $V_{BATT}$  reaches  $V_{OVDIS}$ . However, in such a scenario, the AEM30940 offers the possibility of connecting a primary battery to recharge  $V_{BATT}$  up to  $V_{CHRDY}$ . The transistor M9 connects PRIM to BUFSRC and the transistor M1 is opened to disconnect the SRC input pin as explained in the PRIMARY BATTERY MODE section.

More explanations about the different modes can be found in Section 8.2.

#### 8.1.2. Buck Converter

The buck (or step-down) converter lowers the voltage from  $V_{BOOST}$  to a constant  $V_{BUCK}$  value of 2.2 V. This voltage is available at the BUCK pin. The switching transistors of the buck converter are M5 and M6, with the switching node available externally at SWBUCK. The reactive power components of the buck converter are the external inductor  $L_{BUCK}$  and the external capacitor  $C_{BUCK}$ .



#### 8.1.3. LDO Outputs

Two Low Drop-Out linear regulators are available to supply loads at different operating voltages:

- Through M7, BOOST supplies the high-voltage LDO that powers its load through HVOUT. This regulator delivers a clean voltage named V<sub>HV</sub>. When using the built-in configuration modes, an output voltage of 1.8 V, 2.5 V or 3.3 V can be selected. When using the custom configuration mode, V<sub>HV</sub> is adjustable between 1.8 V and V<sub>OVDIS</sub> 0.3 V. The output is decoupled by the external capacitor C<sub>HV</sub>.
- Through M8, V<sub>BUCK</sub> supplies the low-voltage LDO that powers its load through LVOUT. This regulator delivers a clean voltage named V<sub>LV</sub> of 1.2 V or 1.8 V. The output is decoupled by the external capacitor C<sub>LV</sub>.

See Table 5 for HVOUT and LVOUT maximum current values (respectively I<sub>HV</sub> and I<sub>LV</sub>).

Both the high-voltage and the low-voltage outputs can be dynamically enabled or disabled respectively with the logic control pins ENHV and ENLV (see Table below).

ENLV	LVOUT
L	Disabled
Н	Enabled

ENHV	HVOUT
L	Disabled
Н	Enabled

Table 7: LDOs configurations

## 8.2. Operating Modes

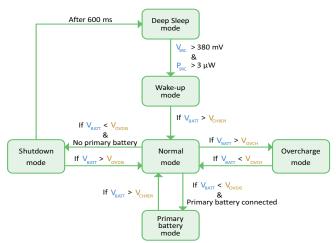


Figure 5: Diagram of the AEM30940 modes

#### 8.2.1. Deep Sleep & Wake Up Modes

The DEEP SLEEP MODE is a state where all nodes are deeply discharged and there is no available energy to be harvested. As soon as the required cold-start voltage of 380 mV and the required power of 3  $\mu$ W becomes available on SRC, the WAKE-UP MODE is activated. For RF sources, the input power at the antenna is defined by the matching network and the associated rectifier (see Section 8.3).  $V_{BOOST}$  and  $V_{BUCK}$  rise up to a voltage of 2.2 V.  $V_{BOOST}$  then rises up to  $V_{OVCH}$ .

At this stage, both LDOs are internally disabled. Therefore, STATUS[0] is low as shown in Figure 11 and Figure 12.

When  $V_{BOOST}$  reaches  $V_{OVCH}$ , two scenarios are possible:

- In the first scenario, a supercapacitor or a capacitor having a voltage lower than V<sub>CHRDY</sub> is connected to the BATT node (see Section 8.2.1.1).
- In the second scenario, a charged battery is connected to the BATT node (see Section 8.2.1.2).

#### 8.2.1.1. Supercapacitor as a Storage Element

If the storage element is a supercapacitor, the storage element may need to be charged from 0 V. The boost converter charges BATT from the input source and by modulating the conductance of M1 and M2. During the charge of the BATT node, both LDOs are disabled and STATUS[0] is set to low. When V<sub>BATT</sub> reaches V<sub>CHRDY</sub>, the circuit enters NORMAL MODE, STATUS[0] is asserted and the LDOs can be enabled by the user using ENLV and ENHV control pins as shown in Figure 11.

#### 8.2.1.2. Battery as a Storage Element

If the storage element is a battery but its voltage is lower than V<sub>CHRDY</sub>, the storage element first needs to be charged until it reaches V<sub>CHRDY</sub>. This allows a safety margin to ensure that the storage element is able to provide the required power before enabling the outputs (LDOs).

Once  $V_{BATT}$  exceeds  $V_{CHRDY}$ , or if the battery was initially charged above  $V_{CHRDY}$ , the circuit enters NORMAL MODE. STATUS[0] is asserted and the LDOs can be dynamically enabled or disabled through ENLV and ENHV as shown in Figure 12.



#### 8.2.2. Normal Mode

Once the AEM enters NORMAL MODE, it stays in this mode as long as the following condition is met:

$$V_{OVDIS} < V_{BATT} < V_{OVCH}$$

The AEM30940 will switch to another mode in the following cases:

- V<sub>BATT</sub> increases above V<sub>OVCH</sub> because the source provides more power than the load consumes. The circuit enters OVERCHARGE MODE, as explained in Section 8.2.3.
- V<sub>BATT</sub> falls below V<sub>OVDIS</sub> due to a lack of power from the source. In this case, either the circuit enters SHUTDOWN MODE as explained in Section 8.2.5, or, if a charged primary battery is connected on PRIM, the circuit enters PRIMARY BATTERY MODE as explained in Section 8.2.4.

#### 8.2.3. Overcharge Mode

When  $V_{BATT}$  reaches  $V_{OVCH}$ , the battery charge is complete. The AEM maintains  $V_{BATT}$  around  $V_{OVCH}$ , with a hysteresis of a few mV as shown in Figure 13, to prevent damage to the storage element and to the internal circuitry. In this configuration, the boost converter is periodically activated to maintain  $V_{BATT}$  and the LDOs are available. Moreover, when the boost converter is not activated, the transistor M1 in Figure 4 is opened to prevent current from the source to the storage element when  $V_{SRC}$  is higher than  $V_{OVCH}$ .

#### 8.2.4. Primary Battery Mode

When V<sub>BATT</sub> drops below V<sub>OVDIS</sub>, the circuit compares the voltage on PRIM with the voltage on FB\_PRIM\_U to determine whether a charged primary battery is connected on PRIM. The voltage on FB\_PRIM\_U is set thanks to two optional resistors as explained in Section 9.3.

If the following formula is true, the circuit considers the primary battery as available and the circuit enters PRIMARY BATTERY MODE.

$$\frac{V_{PRIM}}{4} > V_{FB\_PRIM\_U}$$

In that mode, transistor M1 is opened and the primary battery is connected to BUFSRC through transistor M9 to become the source of energy of the AEM30940. STATUS[1] is asserted as long as the chip is in PRIMARY BATTERY MODE.

The AEM remains in this mode until  $V_{BATT}$  reaches  $V_{CHRDY}$ . At that point, the circuit enters NORMAL MODE.

If no primary battery is used in the application, PRIM, FB\_PRIM\_U and FB\_PRIM\_D must be tied to GND.

#### 8.2.5. Shutdown Mode

When  $V_{BATT}$  drops below  $V_{OVDIS}$  and no power is available from a primary battery, the circuit enters SHUTDOWN MODE, as shown in Figure 14, to prevent deep discharge that could damage the storage element and make the LDOs unstable. The circuit asserts STATUS[1] to warn the application that a shutdown may occur. Both LDO regulators remain enabled during the next 600 ms ( $T_{CRIT}$ ).

If no primary battery is used, this mechanism allows the application circuit, whether it is powered on LVOUT or HVOUT, to trigger an interrupt by the low to-high transition of STATUS[1], and to take all appropriate actions before LVOUT and HVOUT are disabled.

If  $V_{BATT}$  recovers to  $V_{OVDIS}$  within  $T_{CRIT}$  (about 600 ms), the AEM switches back to NORMAL MODE. But if, after  $T_{CRIT}$ ,  $V_{BATT}$  does not reach  $V_{OVDIS}$ , the circuit enters DEEP SLEEP MODE. Both LDOs are disabled and BATT is disconnected from BOOST to avoid damaging the battery due to the overdischarge. From now on, the AEM must go through the wake-up procedure described in the Section 8.2.1.

#### 8.3. Matching Network and Rectifier

To connect AC sources to the AEM30940, an external rectifier is required as well as a matching network in the case of RF energy harvesting.

The goal of the matching network is to modify the impedance relationship between the RF source and the rectifier in order to optimize the power transfer over a frequency band and an input power range.

For RF applications, external high-frequency rectifiers as well as matching networks are available for the following RF bands:

- 828 MHz
- 915 MHz
- 2.4 GHz

Please contact e-peas for more information about matching network and rectifier designs and results.

## 8.4. Maximum Power Point Tracking

During NORMAL MODE, SHUTDOWN MODE and a part of WAKE-UP MODE, the boost converter is regulated thanks to an internal MPPT (Maximum Power Point Tracking) module. V<sub>MPP</sub> is the voltage level of the MPP, and depends on the input power available at the source.

The MPPT module evaluates  $V_{MPP}$  as a constant fraction of the open-circuit voltage of the source  $V_{OC}$ . The ratio between  $V_{MPP}$  and  $V_{OC}$  can be configured with the SELMPP[1:0] pins.



The AEM30940 periodically measures  $V_{OC}$  by stopping to pull current from the source (SRC pin) during  $T_{MPPT,VOC}$  (5.12 ms) every  $T_{MPPT,PERIOD}$  (0.33 s), thus letting the source rise to its open-circuit voltage. The source target voltage  $V_{MPP}$  is then redefined as a fraction of the previously measured  $V_{OC}$ . This way, the MPPT module adapts to the harvester variations due to varying ambient conditions. The behavior of the MPPT module is shown in Figure 6.

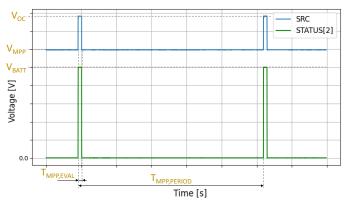


Figure 6: MPP evaluation behavior

With the exception of this sampling process, the source voltage  $V_{SRC}$  is continuously compared to  $V_{MPP}$ :

- When V<sub>SRC</sub> exceeds V<sub>MPP</sub> by a small hysteresis, the boost converter is switched on, extracting electric charges from the source, thus lowering its voltage.
- When V<sub>SRC</sub> falls below V<sub>MPP</sub> by a small hysteresis, the boost converter is switched off, allowing the harvester to accumulate new electric charges into C<sub>SRC</sub>, which voltage rises.

This way, the boost converter regulates its input voltage so that the electric current (or flow of electric charges) that enters the boost converter yields the best power transfer from the harvester under any ambient conditions. The AEM30940 supports any V<sub>MPP</sub> level in the range from 50 mV to 4.5 V. It offers a choice of three values for the V<sub>MPP</sub> / V<sub>OC</sub> ratio through the configuration pins SELMPP[1:0] as shown in Table 9. It is also possible to regulate the source voltage by matching the input impedance of the BOOST converter with an impedance connected to the ZMPP terminal thanks to the ZMPPT feature, by setting SELMPP[1:0] to HH (see Section 9.4). The status of the MPPT controller is reported through one dedicated status pins (STATUS[2]). This status pin is asserted when a MPPT module periodic V<sub>OC</sub> evaluation is being performed.

# 8.5. Storage Element Balancing Circuit for Dual-cell Supercapacitor

When using a dual-cell supercapacitor, it is necessary to keep both cells at similar voltages to avoid damage due to a potential over-voltage on one cell. This is ensured by the AEM30940 storage element balancing circuit.

If a battery, a capacitor or a single-cell supercapacitor is connected on BATT, BAL is connected to GND and the storage element balancing circuit is disabled.

If a dual-cell supercapacitor is connected on BATT, BAL is connected to the node between the two cells of the supercapacitor. The storage element balancing circuit compensates for any mismatch of the two cells that could overcharge one of both cells. It ensures that BAL remains close to  $V_{\rm BATT}$  / 2.



## 9. System Configuration

## 9.1. Battery and LDOs Configuration

Configurations pins		Storage element threshold voltages		LDOs output voltages		Typical use		
CFG[2]	CFG[1]	CFG[0]	V <sub>OVCH</sub>	V <sub>CHRDY</sub>	V <sub>OVDIS</sub>	V <sub>HV</sub>	V <sub>LV</sub>	
Н	Н	Н	4.12 V	3.67 V	3.60 V	3.3 V	1.8 V	Li-ion battery
Н	Н	L	4.12 V	4.04 V	3.60 V	3.3 V	1.8 V	Solid state battery
Н	L	Н	4.12 V	3.67 V	3.01 V	2.5 V	1.8 V	Li-ion/NiMH battery
Н	L	L	2.70 V	2.30 V	2.20 V	1.8 V	1.2 V	Single-cell supercapacitor
L	Н	Н	4.50 V	3.67 V	2.80 V	2.5 V	1.8 V	Dual-cell supercapacitor
L	Н	L	4.50 V	3.92 V	3.60 V	3.3 V	1.8 V	Dual-cell supercapacitor
L	L	Н	3.63 V	3.10 V	2.80 V	2.5 V	1.8 V	LiFePO4 battery
L	L	L	Custom mo	de - Program	mable throug	h R1 to R6.	1.8 V	

Table 8: Usage of CFG[2:0]

Through three configuration pins (CFG[2:0]), the user can set a particular operating mode from a range that covers most application requirements, without any dedicated external component as shown in Table 8. The three threshold levels are defined as:

- V<sub>OVCH</sub>: maximum voltage accepted on the storage element before disabling the boost converter.
- V<sub>CHRDY</sub>: minimum voltage required on the storage element after a cold start before enabling the LDOs.
- V<sub>OVDIS</sub>: minimum voltage accepted on the storage element before considering the storage element as depleted.

See Section 8 for more information about the purposes of these thresholds.

The two LDOs output voltages are called  $V_{HV}$  and  $V_{LV}$  for the high and low output voltages respectively. Seven combinations of these voltage levels are hard-wired and selectable through the CFG[2:0] configuration pins, covering most application cases. For other  $V_{OVCH}$ ,  $V_{CHRDY}$ ,  $V_{OVDIS}$  and  $V_{HV}$  voltages combinations, a custom mode is available. In this mode, the user can define those voltages with resistors, connected to the pins named SET\_OVDIS, SET\_CHRDY, SET\_OVCH and FB\_HV.

When the custom mode is not used, SET\_OVDIS, SET\_CHRDY and SET\_OVCH pins must be connected to  $V_{BUCK}$  and FB\_HV must be left floating.

#### 9.1.1. Custom Mode

When CFG[2:0] are tied to GND, the custom mode is selected. All six resistors, shown in Figure 7, are used to configure the custom mode as follows:

 $V_{\rm OVCH}$ ,  $V_{\rm CHRDY}$  and  $V_{\rm OVDIS}$  are defined thanks to R1, R2, R3 and R4. The resistors are calculated as follows:

$$- R_T = R1 + R2 + R3 + R4$$

- 
$$1M\Omega \le R_T \le 100M\Omega$$

- R1 = 
$$R_T \cdot \frac{1V}{V_{OVCH}}$$
  
- R2 =  $R_T \cdot \left(\frac{1V}{V_{CHRDY}} - \frac{1V}{V_{OVCH}}\right)$   
- R3 =  $R_T \cdot \left(\frac{1V}{V_{OVDIS}} - \frac{1V}{V_{CHRDY}}\right)$   
- R4 =  $R_T \cdot \left(1 - \frac{1V}{V_{OVDIS}}\right)$ 

V<sub>HV</sub> is defined thanks to R5 and R6. The resistive divider is configured as follows:

$$- R_V = R5 + R6$$

- 
$$1M\Omega \le R_V \le 40M\Omega$$

$$- R5 = R_V \cdot \frac{1V}{V_{HV}}$$

$$- R6 = R_V \cdot \left(1 - \frac{1V}{V_{HV}}\right)$$

NOTE: If ENHV = L (HVOUT is disabled), R5 and R6 are not needed,  $FB_{\_}HV$  should be left floating.



The resistors should have high values to make the current flowing through them negligible. Moreover, the following constraints must be met to ensure the functionality of the chip:

- $V_{CHRDY} + 0.05V \le V_{OVCH} \le 4.5V$
- $V_{OVDIS} + 0.05V \le V_{CHRDY} \le V_{OVCH} 0.5V$
- 2.2V ≤ V<sub>OVDIS</sub>
- $V_{HV} \le V_{OVDIS} 0.3V$

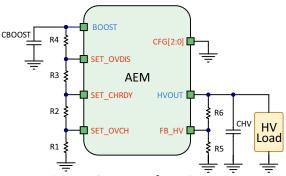


Figure 7: Custom configuration resistors

## 9.2. MPPT Configuration

Two dedicated configuration pins, SELMPP[1:0], allow selecting the MPP tracking ratio based on the characteristic of the input power source.

SELMPP[1]	SELMPP[0]	$V_{MPP}/V_{OC}$
L	L	50%
L	Н	65%
Н	L	80%
Н	Н	ZMPP

Table 9: Usage of SELMPP[1:0]

#### 9.3. Primary Battery Configuration

To use the primary battery, it is mandatory to determine V<sub>PRIM,MIN</sub>, the voltage at which the primary battery is considered as fully depleted. The circuit uses a resistive divider between BUCK and FB\_PRIM\_D to define the voltage on FB\_PRIM\_U as V<sub>PRIM,MIN</sub> divided by 4. During V<sub>PRIM,MIN</sub> evaluation, the circuit connects FB\_PRIM\_D to GND.

When V<sub>PRIM,MIN</sub> is not evaluated, FB\_PRIM\_D is left floating to avoid quiescent current on the resistive divider. The resistors are calculated as follows:

- $R_p = R7 + R8$
- $100 \text{k}\Omega \leq R_p \leq 500 \text{k}\Omega$
- $R7 = \frac{V_{PRIM\_MIN}}{4} \cdot R_p \cdot \frac{1}{2.2V}$
- $R8 = R_{D} R7$

NOTE: FB\_PRIM\_U, FB\_PRIM\_D and PRIM must be tied to GND if no primary battery is used.

## 9.4. ZMPPT Configuration

Instead of working at a ratio of the open-circuit voltage, the AEM30940 can regulate the input impedance of the BOOST converter so that it matches a constant impedance connected to the ZMPP pin ( $R_{ZMPP}$ ). In this case, the AEM30940 regulates  $V_{SRC}$  at a voltage equal to the product of the ZMPP impedance and the current available at the SRC input.

$$-10\Omega \le R_{7MDD} \le 1M\Omega$$

#### 9.5. No-battery Configuration

If the application doesn't use a storage element, the PCB must include a capacitor on the BATT pin. See Section 9.7 for  $C_{\text{BATT}}$  value.

The storage element may not be necessary in the following cases:

- If the harvested energy source is permanently available and covers the application purposes.
- If the application does not need to store energy when the harvested energy source is not available.

# 9.6. Supplying an Application Circuit with BUCK

It is possible to supply an application circuit directly from BUCK, with the benefit of high BATT to BUCK efficiency, provided that the following conditions are met:

- The application circuit can be supplied from a voltage in the 2.0 V - 2.5 V range (V<sub>BUCK</sub> is typically 2.2 V with ripple, see Table 5).
- The sum of the following currents must be below the maximum I<sub>BUCK</sub> value (see Table 5):
  - Current of the load connected to BUCK.
  - Current of the load connected to LVOUT.
- The application circuit on BUCK does not pull current during the AEM30940 cold start.



To satisfy the last condition, the following circuit may be implemented:

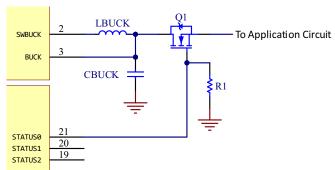


Figure 8: Schematic for supplying an application circuit with BUCK

Q1 is a N-MOSFET, whose gate is driven by STATUS[0] with R1 as a pull-down resistor. When the AEM30940 is in DEEP SLEEP MODE or in WAKE-UP MODE, STATUS[0] is LOW (see Section 8.2), ensuring that Q1 is non-conducting, and thus that the application circuit is not supplied.

When the AEM30940 switches from WAKE-UP MODE to NORMAL MODE, STATUS[0] is HIGH, making Q1 conducting. The application circuit is then supplied by BUCK, and remains so when the AEM30940 is in NORMAL MODE, OVERCHARGE MODE, PRIMARY BATTERY MODE and SHUTDOWN MODE.

Q1 must be chosen as follows:

- Low Gate-Source Leakage I<sub>GSS</sub>.
- Low Zero Gate Voltage Drain Current IDSS.
- Drain-Source On-State Resistance R<sub>DS(on)</sub> low enough to supply application circuit with an acceptable voltage drop.
- $V_{GS}$  maximum voltage must be above  $V_{OVCH}$  (STATUS[0] HIGH voltage is  $V_{BOOST}$ ).
- Maximum gate-source threshold voltage V<sub>GS(th),MAX</sub> matches the following, with V<sub>BUCK,MAX</sub> being V<sub>BUCK</sub> maximum value stated in Table 5:

$$V_{GS(th),MAX} < V_{OVDIS} - V_{BUCK,MAX}$$

## 9.7. Storage Element Information

The energy storage element of the AEM30940 can be a rechargeable battery, a supercapacitor or a large capacitor. It should be chosen so that its voltage does not fall below  $V_{\text{OVDIS}}$  even during occasional peaks of the load current. If the internal resistance of the storage element cannot sustain this voltage limit, it is advisable to buffer the battery by decoupling it with a capacitor.

The BATT pin, connecting the storage element, must never be left floating. If the application expects a disconnection of the battery (e.g., because of a user removable connector), the PCB must include a capacitor:

- If the LDOs are used, the minimum needed capacitor value is 150  $\mu F$ .
- If the LDOs are not used, the minimum needed capacitor value is 22  $\mu F$ .

The leakage current of the storage element should be small as leakage currents directly impact the quiescent current of the subsystem.

#### 9.8. External Inductors Information

The AEM30940 operates with two standard miniature inductors. Switching frequency must be at least 10 MHz for both. Low equivalent series resistance (ESR) favors the power conversion efficiency of the boost and buck converters.

#### L<sub>BOOST</sub>

The AEM30940 circuit is typically implemented with one of the following values on L<sub>ROOST</sub>:

- $10\,\mu\text{H}$  (peak current min. 250 mA) allows higher current from SRC to BATT.
- 22 μH (peak current min. 115 mA) allows better efficiencies, especially at low SRC voltages.

#### L<sub>BUCK</sub>

The buck inductor  $L_{BUCK}$  must sustain a peak current of at least 50 mA. The recommended value is 10  $\mu$ H.



## 9.9. External Capacitors Information

The AEM30940 operates with:

- Four identical standard miniature ceramic capacitors of 10  $\mu\text{F}.$
- One miniature ceramic capacitor of 22  $\mu$ F.

The leakage current of the capacitors should be small as leakage currents directly impact the quiescent current of the subsystem.

#### $C_{SRC}$

This capacitor acts as an energy buffer at the input of the boost converter. It prevents large voltage fluctuations of  $V_{SRC}$  when the boost converter is switching. The recommended value is 10  $\mu$ F +/- 20%.

#### $C_{BUCK}$

This capacitor acts as an energy buffer for the buck converter. It also reduces the voltage ripple induced by the current pulses inherent to the switching mode of the converter. The recommended value is  $10 \, \mu F$  +/- 20%.

#### **C**BOOST

This capacitor acts as an energy buffer for the boost converter. It also reduces the voltage ripple induced by the current pulses inherent to the switching mode of the converter. The recommended value is  $22 \mu F +/-20\%$ .

#### C<sub>HV</sub> / C<sub>LV</sub>

These capacitors ensure a high-efficiency load regulation of the high-voltage and low-voltage LDO regulators. Closed-loop stability requires the value to be in the range of 8  $\mu$ F to 14  $\mu$ F.



## 10. Typical Application Circuits

#### 10.1. Example Circuit 1

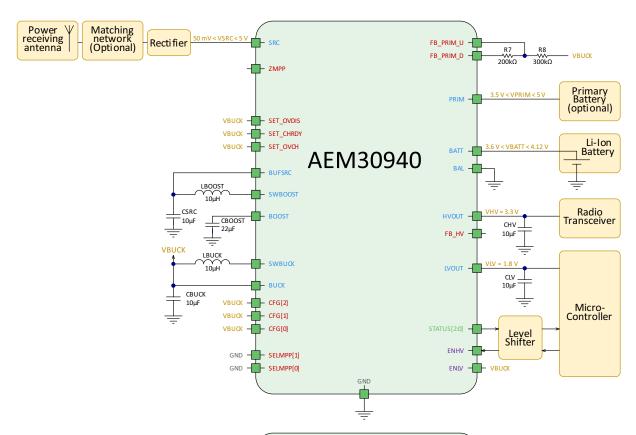


Figure 9: Typical application circuit 1

The energy source is a RF source and the storage element is a standard Li-ion battery cell. The radio communication is supplied by HVOUT set at 3.3 V. The micro-controller that controls the application is supplied by LVOUT set at 1.8 V.

This circuit uses a pre-defined AEM configuration, typical of systems that use standard components for radio and energy storage.

The operating mode pins are set as follows:

-  $CFG[2:0] = HHH (all to V_{BUCK})$ 

Referring to Table 8, in this mode, the threshold voltages are:

- V<sub>OVCH</sub> = 4.12 V
- V<sub>CHRDY</sub> = 3.67 V
- V<sub>OVDIS</sub> = 3.60 V

Moreover, the LDOs output voltages are:

- $V_{HV} = 3.3 V$
- V<sub>LV</sub> = 1.8 V

A primary battery is also connected as a back-up solution. The minimal level allowed on this battery is set at 3.5 V. Following equations from Section 9.3:

$$-R_{\rm p}=0.5M\Omega$$

$$- \quad \mathsf{R7} \, = \, \frac{\mathsf{3.5V}}{\mathsf{4}} \cdot \mathsf{0.5M}\Omega \cdot \frac{\mathsf{1}}{\mathsf{2.2V}} \, = \, \mathsf{200k}\Omega$$

- 
$$R8 = 0.5M\Omega - 200k\Omega = 300k\Omega$$

The MPP configuration pins SELMPP[1:0] are tied to GND (logic LOW), thus, selecting an MPP ratio of 50%.

The LVOUT LDO output is enabled by tying ENLV to BUCK.

The micro-controller is supplied by LVOUT, that is enabled when  $V_{BATT}$  and  $V_{BOOST}$  voltage rise above  $V_{CHRDY}$ .

The application software can enable or disable the radio transceiver supply with a GPIO connected to ENHV.



#### 10.2. Example Circuit 2

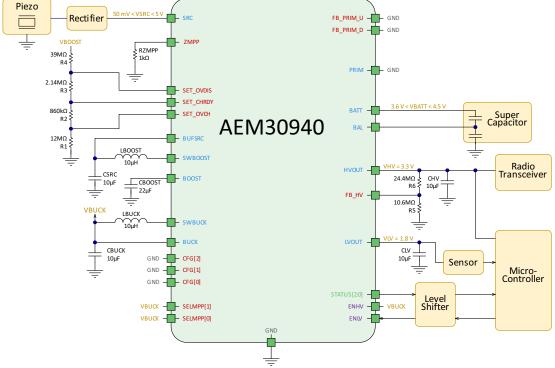


Figure 10: Typical application circuit 2

The energy source is a piezo source and the storage element is a dual-cell supercapacitor. Please note that the supercapacitor might be completely depleted during the cold start.

Moreover, BAL is connected to the dual-cell supercapacitor to compensate for any mismatch between the two cells and, in that way, protect the supercapacitor.

A micro-controller acts as the application master. The operating mode pins are set as follows:

- CFG[2:0] = LLL (all to GND)

The storage element voltages are set as follows with a custom configuration:

- V<sub>OVCH</sub> = 4.5 V
- V<sub>CHRDY</sub> = 4.2 V
- $V_{OVDIS} = 3.6 V$

 $R_T$  is set to 54 M $\Omega$ . R1, R2, R3 and R4 values are computed from the equations in Section 9.1.1:

- R1 = 
$$54M\Omega \cdot \frac{1V}{4.5V} = 12M\Omega$$

- R2 = 
$$54M\Omega \cdot \left(\frac{1V}{4.2V} - \frac{1V}{4.5V}\right) = 860k\Omega$$

- R3 = 
$$54M\Omega \cdot \left(\frac{1V}{3.5V} - \frac{1V}{4.2V}\right) = 2.14M\Omega$$

- R4 = 
$$54M\Omega \cdot \left(1 - \frac{1V}{3.5V}\right) = 39M\Omega$$

The LDO voltages are set as follows:

Enabling and disabling LVOUT is controlled by the application circuit with a micro-controller GPIO connected to ENLV.

ENHV is tied to BUCK so that HVOUT is always on.

 $R_V$  is set to 35 M $\Omega$ . R5 and R6 are determined by applying the equations found in Section 9.1:

- R5 = 
$$35M\Omega \cdot \frac{1V}{3.3V} = 10.6M\Omega$$

- R6 = 
$$35M\Omega \cdot \left(1 - \frac{1V}{3.3V}\right) = 24.4M\Omega$$

The micro-controller is supplied by HVOUT, which is enabled when  $V_{BATT}$  and  $V_{BOOST}$  voltages rise above  $V_{CHRDY}$ .

The MPP configuration pins SELMPP[1:0] are tied to BUCK (logic HIGH), thus, selecting the ZMPPT configuration to match a  $1-k\Omega$  impedance.

No primary battery is connected: PRIM, FB\_PRIM\_U and FB PRIM D pins are tied to GND.



## 11. Circuit Behavior

#### 11.1. Cold-start Behavior

#### 11.1.1. (Super)capacitor as a Storage Element

The following figure shows the AEM30940 behavior with a capacitor connected to BATT and the following settings:

- CFG[2:0] = LHH
- SELMPP[1:0] = HL (80%)
- C<sub>BATT</sub> = 4.85 mF
- SRC: 1 mA current source with 3 V voltage compliance
- ENHV = ENLV = H
- 22 kΩ resistive load on LVOUT
- $2 k\Omega$  resistive load on HVOUT

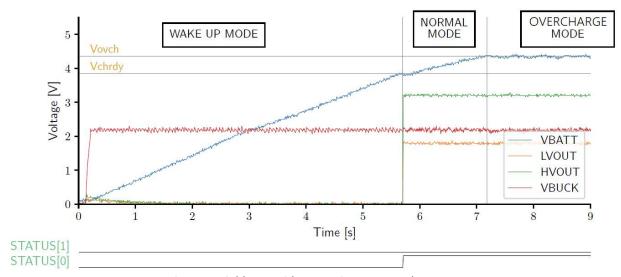


Figure 11: Cold start with a capacitor connected to BATT



#### 11.1.2. Battery as a Storage Element

The following figure shows the AEM30940 behavior with a pre-charged capacitor (acting as a battery) connected to BATT and the following settings:

- CFG[2:0] = LHH
- SELMPP[1:0] = HL (80%)
- $C_{BATT} = 4.85 \text{ mF}$
- SRC: 1 mA current source with 3 V voltage compliance
- ENHV = ENLV = H
- 22 kΩ resistive load on LVOUT
- $2 k\Omega$  resistive load on HVOUT

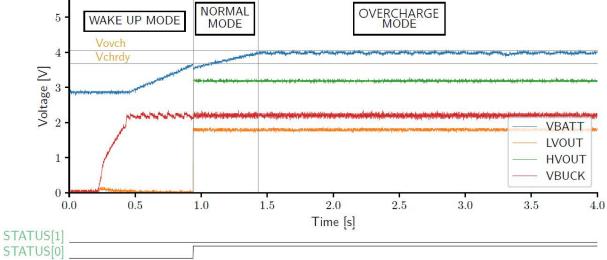


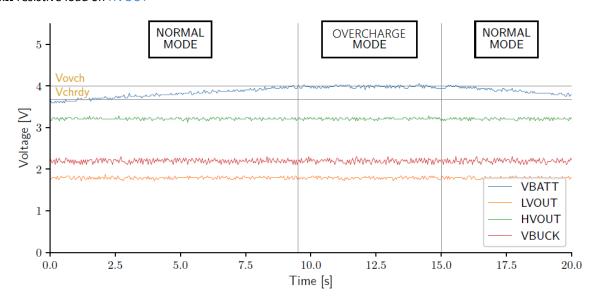
Figure 12: Cold start with a battery connected to BATT



## 11.2. Overcharge Mode Behavior

The following figure shows the AEM30940 behavior in OVERCHARGE MODE with the following settings:

- CFG[2:0] = HHH
- SELMPP[1:0] = HL (80%)
- C<sub>BATT</sub> = 4.85 mF
- SRC: 1 mA current source with 3 V voltage compliance
- ENHV = ENLV = H
- 22 kΩ resistive load on LVOUT
- $2 k\Omega$  resistive load on HVOUT



STATUS[1] STATUS[0]

Figure 13: Overcharge mode

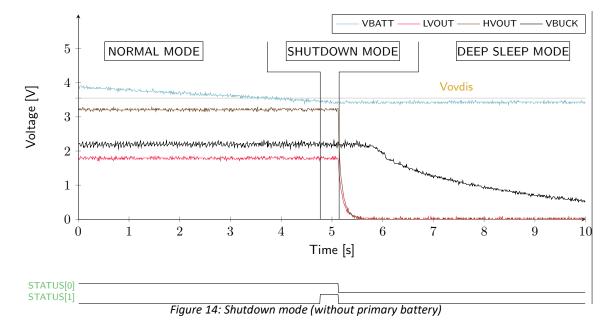


#### 11.3. Shutdown Mode Behavior

#### 11.3.1. Without Primary Battery

The following figure shows the AEM30940 behavior in SHUTDOWN MODE with the following settings:

- CFG[2:0] = LHL
- SELMPP[1:0] = HL (80%)
- $C_{BATT} = 4.85 \text{ mF}$
- SRC: left floating to let the storage element on BATT discharge
- ENHV = ENLV = H
- $22 \text{ k}\Omega$  resistive load on LVOUT
- $22 \text{ k}\Omega$  resistive load on HVOUT
- PRIM, FB\_PRIM\_U and FB\_PRIM\_D connected to GND

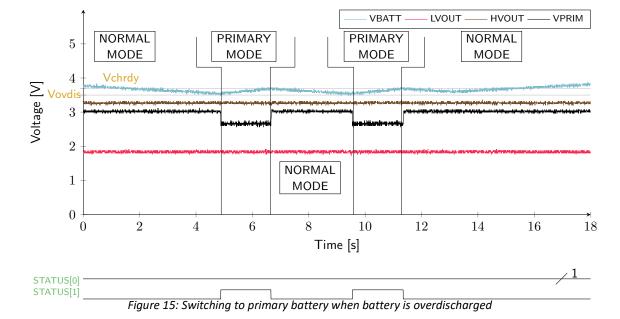




#### 11.3.2. With Primary Battery

The following figure shows the AEM30940 behavior in SHUTDOWN MODE with the following settings:

- CFG[2:0] = HHH
- SELMPP[1:0] = HL (80%)
- $C_{BATT} = 4.85 \text{ mF}$
- SRC: left floating to let the storage element on BATT discharge
- ENHV = ENLV = H
- $22 \text{ k}\Omega$  resistive load on LVOUT
- 22 kΩ resistive load on HVOUT
- PRIM: 3 V voltage source with 1 mA current compliance
- $R7 = 68 \text{ k}\Omega$
- $R8 = 330 \text{ k}\Omega$





## 12. Performance Data

## 12.1. BOOST Conversion Efficiency for LBOOST = 10 $\mu$ H

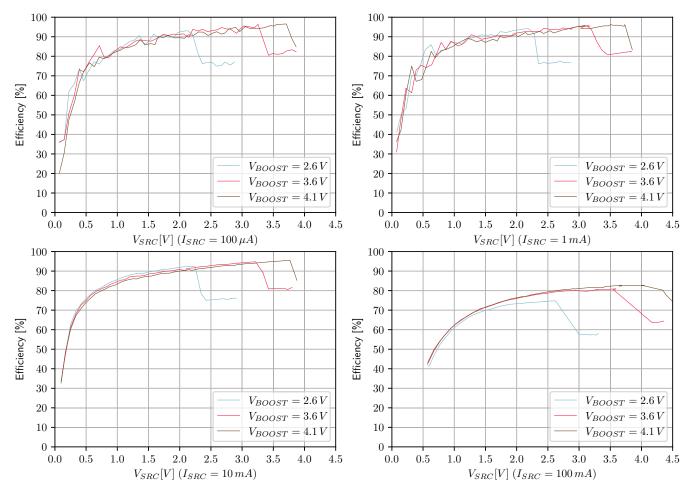


Figure 16: Boost efficiency for Isrc at  $100\mu\text{A}$ , 1mA, 10mA and 100mA (LBOOST =  $10~\mu\text{H}$ )



## 12.2. BOOST Conversion Efficiency for LBOOST = 22 $\mu$ H

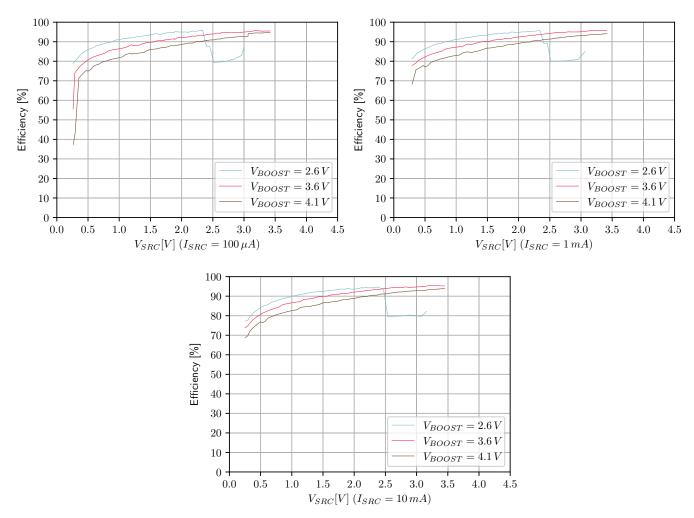


Figure 17: Boost efficiency for Isrc at  $100\mu A$ , 1mA and 10mA (LBOOST =  $22 \mu H$ )



## 12.3. BUCK Conversion Efficiency

The following graph shows the buck converter efficiency from BATT to BUCK with the AEM30940 quiescent current  $I_Q$  subtracted.

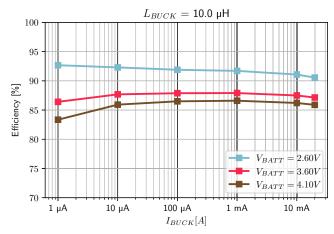


Figure 18: Buck Efficiency ( $L_{BUCK} = 10 \mu H$ )

## 12.4. Quiescent Current

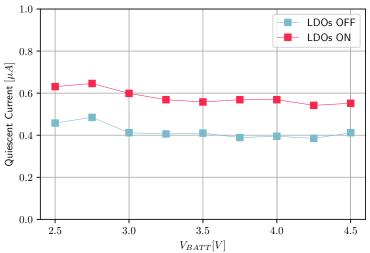
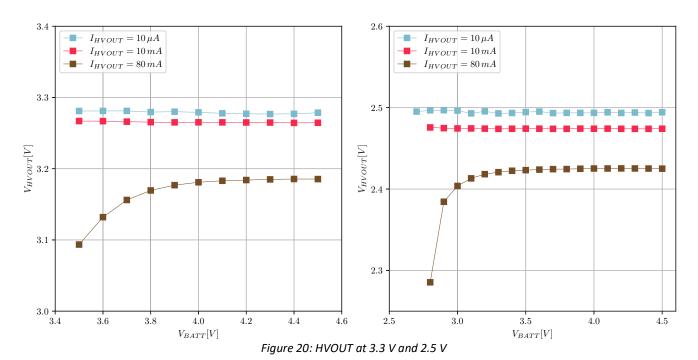


Figure 19: Quiescent current with LDOs on and off



## 12.5. High-voltage LDO Regulation



## 12.6. Low-voltage LDO Regulation

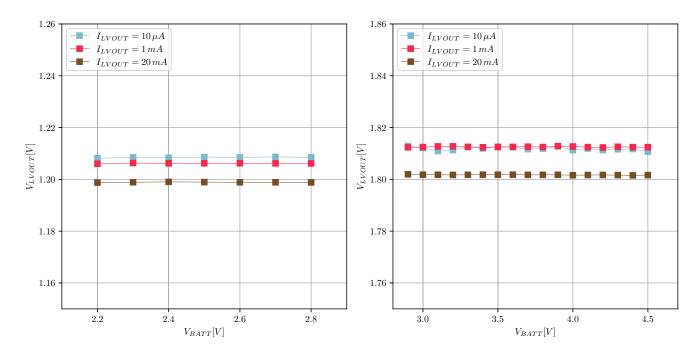


Figure 21: LVOUT at 1.2 V and 1.8 V



## 12.7. High-voltage LDO Efficiency

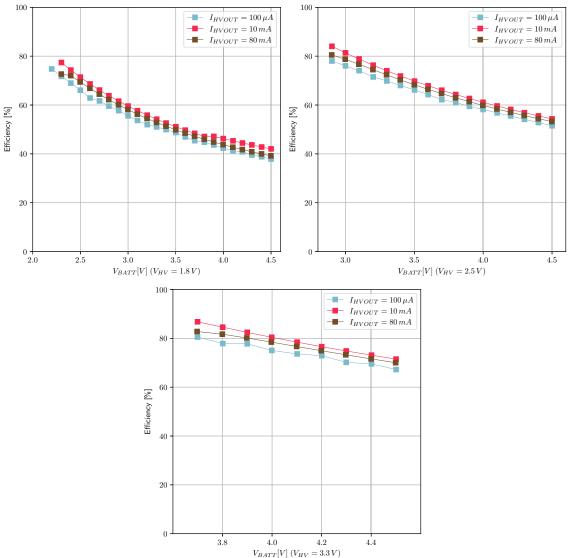


Figure 22: HVOUT efficiency at 1.8V, 2.5V and 3.3 V

The theoretical efficiency of an LDO can be calculated as Vout / Vin if quiescent current can be neglected with regards to the output current. For the high-voltage LDO, the theoretical efficiency is equal to  $V_{HV}$  /  $V_{BATT}$ .



## 12.8. Low-voltage LDO Efficiency

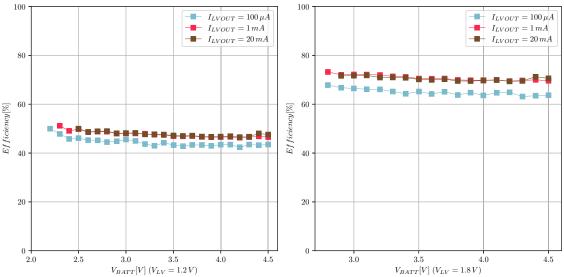


Figure 23: Efficiency of buck cascaded with LVOUT at 1.2 V and 1.8 V

The theoretical efficiency of an LDO can be calculated as  $V_{LV} / V_{BUCK}$ . Starting from the battery, the efficiency of the buck converter (nbuck) has to be taken into account (see Figure 4).

The efficiency between  $\mathbf{V}_{\mathrm{BATT}}$  and  $\mathbf{V}_{\mathrm{LV}}$  is therefore equal to:

$$\eta_{BUCK} \cdot \frac{V_{LV}}{V_{BUCK}}$$



## 13. Schematic

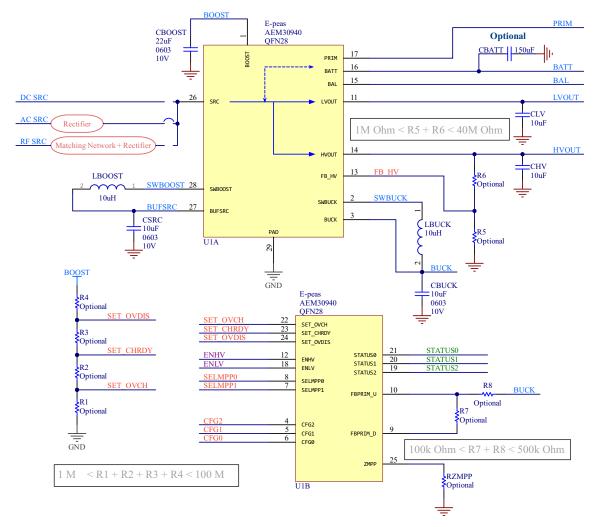


Figure 24: Schematic example

Designator	Description	Quantity	Manufacturer	Part Number
U1	AEM30940	1	e-peas	order at sales@e-peas.com
L <sub>BOOST</sub>	Power Inductor 10 μH - 0,90 A - LPS4018	1	Coilcraft	LPS4018-103MR
L <sub>BOOST</sub> (alt.)	Power Inductor 10 μH - 0,84 A - 3015	1	Würth	744 040 321 00
L <sub>BOOST</sub> (alt.)	Power Inductor 22 μH - 0,65 A - LPS4018	1	Coilcraft	LPS4018-223MR
C <sub>BOOST</sub>	Ceramic Cap 22 μF, 10 V, 20%, X5R, 0603	1	Murata	GRM188R61A226ME15D
L <sub>BUCK</sub>	Power Inductor 10 μH - 0,25 A - 0603	1	TDK	MLZ1608M100WT
C <sub>BUCK</sub>	Ceramic Cap 10 μF, 10 V, 20%, X5R, 0603	1	TDK	C1608X5R1A106M080AC
C <sub>SRC</sub>	Ceramic Cap 10 μF, 10 V, 20%, X5R, 0603	1	TDK	C1608X5R1A106M080AC
C <sub>HV</sub>	Ceramic Cap 10 μF, 25 V, 10%, X7S, 0805	1	TDK	C2012X7S1E106K125AE
C <sub>LV</sub>	Ceramic Cap 10 μF, 10 V, 20%, X5R, 0603	1	TDK	C1608X5R1A106M080AC
C <sub>BATT</sub>	Ceramic Cap 150 μF, 6.3 V, 20%, X5R, 1206	1	TDK	GRM31CR60J157ME11L

Table 10: BOM example for AEM30940 and its required passive components



## 14. Layout

#### 14.1. Guidelines

Good layout practices are mandatory in order to obtain good AEM30940 stability, best efficiency and avoid EMI problems.

The following list, while not exhaustive, shows the main attention points when routing a PCB with the AEM30940:

- The switching nodes (BUFSRC, SWBOOST, SWBUCK and BUCK) must be kept as short as possible, with minimal track resistance and minimal track capacitance. Low resistance is obtained by keeping track length as short as possible and track width as large as possible between these switching nodes and the AEM30940 pins. Minimal capacitance is obtained by maintaining a large distance between the switching nodes and other signals. We recommend removing the ground plane, the power plane and the bottom layer ground pour under LBOOST and LBUCK footprints, as well as adding distance between BUFSRC/SWBOOST and the top ground pour, as shown in Figure 25.
- The decoupling capacitors (C<sub>BOOST</sub> C<sub>BUCK</sub> C<sub>SRC</sub> C<sub>HV</sub> C<sub>LV</sub> C<sub>BATT</sub>) must be placed as close as possible to the AEM30940, with direct connection and minimum track resistance for the corresponding power nodes (BOOST, BUCK, BUFSRC, HVOUT, LVOUT and BATT).

- The GND return path between the decoupling capacitors and the AEM30940 thermal pad, which is the AEM30940 main GND connection, must be as direct and short as possible. This is preferably done on the top layer when possible, otherwise by internal/bottom plane, using low resistance vias to decrease layer-to-layer connection resistance. In Figure 25, this GND return path is done on an internal plane.
- The external DC power connections (SRC, HVOUT, LVOUT and BATT) must be connected to the AEM30940 with low resistance tracks.
- If used, ZMPP must be connected to the AEM30940 with a low resistance track, according to the expected SRC power.
- The BAL pin connection track must be able to handle at least 40 mA.
- The custom mode setting pins SET\_OVDIS, SET\_CHRDY and SET\_OVCH are high impedance analog inputs typically connected to a resistive divider with high resistor values, making those three nodes prone to pickup noise. Thus, it is recommended to keep those as short as possible and as far as possible to noise sources such as DCDC switching nodes.
- The configuration pins and the status pins have minimal layout restrictions.



## 14.2. Layout Example

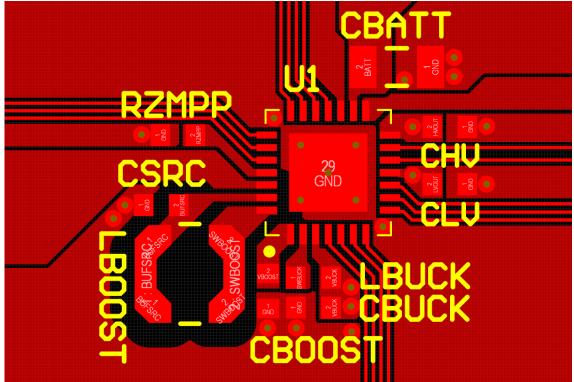


Figure 25: Layout example for the AEM30940 and its passive components



## 15. Package Information

## 15.1. Plastic Quad Flatpack No-lead (QFN 28-pin 5x5mm)

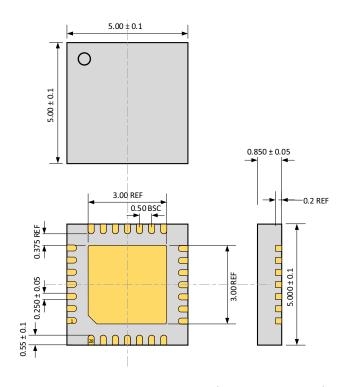


Figure 26: QFN 28-pin 5x5mm drawing (all dimension in mm)

## 15.2. Board Layout (QFN 28-pin 5x5mm)

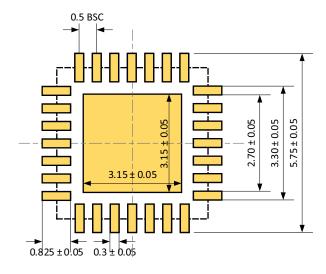


Figure 27: Recommended board layout for QFN 28-pin 5x5mm (all dimension in mm)



## 16. Glossary

**AEM** 

Ambient Energy Manager.

вом

Bill Of Materials.

 $C_{BATT}$ 

Capacitor connected on the BATT pin (if no storage element connected).

**C**BOOST

Output capacitor of the BOOST converter.

**C**BUCK

Output capacitor of the BUCK converter.

 $C_{HV}$ 

High-voltage LDO regulator decoupling capacitor.

 $C_{LV}$ 

Low-voltage LDO regulator decoupling capacitor.

**C**SRC

**BUFSRC** pin decoupling capacitor.

**GPIO** 

General Purpose Input / Output.

**I**BUCK

Total load current supplied by the BUCK converter (including the LVOUT current  $I_{IV}$ ).

 $I_{HV}$ 

Load current supplied by the high-voltage LDO regulator.

I<sub>LV</sub>

Load current supplied by the low-voltage LDO regulator.

I<sub>PRIM</sub>

Current from the primary battery.

lo

Quiescent current on BATT when no energy is available on SRC.

I<sub>SRC</sub>

Harvested current from the energy source.

L<sub>BOOST</sub>

BOOST converter inductor.

**L**BUCK

BUCK converter inductor.

LDO

Low Drop-Out.

**MPPT** 

Maximum Power Point Tracking.

**PCB** 

Printed Circuit Board.

P<sub>SRC\_CS</sub>

Minimum power available on SRC for the AEM30940 to coldstart.

 $R_{P}$ 

Sum of resistors for setting the primary battery minimum voltage.  $R_p = R7 + R8$ .

R-

Sum of resistors for setting the battery protection threshold voltages in custom mode.  $R_T = R1 + R2 + R3 + R4$ .

 $\mathbf{R}_{\mathbf{V}}$ 

Sum of resistors for setting the output voltage of the high-voltage LDO in custom mode. R<sub>V</sub> = R5 + R6.

**R**<sub>ZMPP</sub>

Resistor that defines the AEM30940 BOOST converter input resistance when used in ZMPP mode.

**T**CRIT

Time before shutdown once STATUS[1] has been asserted.

T<sub>MPPT,VOC</sub>

Open-circuit duration for the MPP evaluations.

T<sub>MPPT,PERIOD</sub>

Time between two MPP evaluations.

 $V_{BATT}$ 

Voltage on the **BATT** pin.

**V**BOOST

Output voltage of the BOOST converter.

**V**BUCK

Output voltage of the BUCK converter.

**V<sub>CHRDY</sub>** 

Charge ready voltage on the BATT pin.

V<sub>FB\_PRIM\_U</sub>

Feedback for the minimal voltage level on the primary battery.

 $\mathbf{V}_{\mathsf{HV}}$ 

Output voltage of the high-voltage LDO regulator.



 $\mathbf{V}_{\mathsf{LV}}$ 

Output voltage of the low-voltage LDO regulator.

## $\mathbf{V}_{\mathbf{MPP}}$

Target regulation voltage on SRC when extracting power.

## $v_{oc}$

Open-circuit voltage of the harvester connected to the SRC pin.

#### **V**<sub>OVCH</sub>

Over-charge voltage on the BATT pin.

#### **V<sub>OVDIS</sub>**

Over-discharge voltage on the BATT pin.

#### $V_{PRIM}$

Voltage on the primary battery.

#### V<sub>PRIM MIN</sub>

Voltage at which the primary battery is considered fully depleted.

## $\mathbf{V}_{\text{SRC}}$

Voltage on the SRC pin.

## **ZMPPT**

Maximum Power Point Tracking with constant impedance.



# 17. Revision History

Revision	Date	Description
1.0	July, 2018	Creation of the document.
1.2	June, 2019	<ul> <li>Efficiencies measurements updated.</li> <li>ESD specifications.</li> <li>HVOUT voltage changed from 4.2 V to 4.1 V in Figure 3.</li> <li>AC source instead of Power receiving antenna for the front page Figure and the Figures 1, 3 and 4.</li> </ul>
1.3	November, 2020	<ul> <li>Performances efficiency curves added for the 2450 MHz frequency band.</li> <li>ESD qualification added.</li> <li>Changed from "cold-start" or "coldstart" to "cold start" throughout the document.</li> </ul>
1.4	June, 2022	CBUCK value changed from 10 μF to 22 μF.
1.5	December, 2023	<ul> <li>Term "Balun" replaced by "Storage Element Balancing Circuit".</li> <li>Term "OVERVOLTAGE mode" replaced by "OVERCHARGE mode".</li> <li>External component names color changed to orange instead of blue.</li> <li>RF input power values and efficiency graphs removed and placed in an app note.</li> <li>First page:  - Maximum MPPT voltage operation range corrected to 4.5 V.</li> <li>SET_OVCH and SET_OVDIS swapped on AEM diagram.</li> <li>Link to e-peas website added for evaluation boards information.</li> <li>Table of contents, list of Figures and list of Tables widths changed to page width.</li> <li>Aesthetic changes in Figures 1, 2, 3, 4, 8, 24, 26, 27 and on Table 7.</li> <li>"See page" column removed from Table 1.</li> <li>Added all AEM pins in the Absolute Maximum Ratings table.</li> <li>Added "Pin Configuration and Functions" section with pinout diagram and functions.</li> <li>SET_OVCH, SET_CHRDY and SET_OVDIS pins changed from "left floating" to "connected to BUCK" when not used in Table 1 and in Section 9.1.</li> <li>Voltage on BATT and PRIM added in Absolute Maximum Ratings table.</li> <li>Table S:</li> <li>Footnotes added.</li> <li>VMPP minimum and maximum values added.</li> <li>ISRC value added for LBOOST value of 22 μH.</li> <li>Different min values for VBATT depending on used storage element removed.</li> <li>VHV maximum value changed from "VBATT -0.3 V" to "VOVDIS - 0.3 V".</li> <li>Added IBUCK, IQ, TMPPT.VOC and TMPPT.PERIOD.</li> <li>Table 6:</li> <li>CSRC maximum value changed from 150 μF to 22 μF.</li> <li>LBOOST, CBOOST and CBUCK maximum values removed.</li> <li>CBUCK min and typical values modified from 15 μF and 22 μF to 8 μF and 10 μF.</li> <li>ENHV minimum and maximum values removed.</li> <li>CBUCK min and typical values modified from 15 μF and 22 μF to 8 μF and 10 μF.</li> <li>ENHV minimum and maximum values removed.</li> <li>CBUCK min and typical values modified from 15 μF and 22 μF to 8 μF and 10 μF.</li> <li>ENHV minimum and maximum value changed rom solved to value figure and t</li></ul>

Table 11: Revision history